

[Name of Document] ABSTRACT OF THE DISCLOSURE

[Abstract]

[Object] To provide a positive resist composition suitable for the case using an exposure light source of 160 nm or less, particularly a F₂ excimer laser ray (157 nm). More specifically, to provide a positive resist composition capable of exhibiting sufficiently high transparency on use of a light source at 157 nm and satisfying the properties with respect to the coatability and the development defect; further capable of forming a pattern with good sensitivity and high resolution, and ensuring excellent dry etching resistance..

[Construction] A positive resist composition comprising:

(A) a fluorine group-containing resin having: a structure wherein at least one of the main chain and the side chain of the polymer skeleton has at least one fluorine atom; and having a group capable of decomposing under the action of an acid to increase the solubility in an alkali developer;

(B) a compound capable of generating an acid upon irradiation with one of actinic ray and radiation, and

(C) a surfactant containing at least one of a silicon atom and a fluorine atom.

[Selected Drawing] None